

*MDS170L* 170 Watts, 36 Volts, Pulsed Avionics 1030/1090 MHz

<b>GENERAL DESCRIPTION</b> The MDS170L is a high power COMMON E designed for pulsed systems in the frequency transistor includes input and output prematch device has gold thin-film metallization and d highest MTTF. Low thermal resistance Solo junction temperature, extends life.	CASE OUTLINE 55KT, STYLE 1	
ABSOLUTE MAXIMUM I Maximum Power Dissipation @ 25°C <sup>2</sup>	RATINGS 350 Watts	
Maximum Voltage and CurrentBVcesCollector to Base VoltageBVeboEmitter to Base VoltageIcCollector CurrentMaximum TemperaturesStorage TemperatureOperating Junction Temperature	50 Volts 3.5 Volts 15 Amps - 65 to + 200°C + 200°C	

## ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg η <sub>c</sub> VSWR	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 1030 - 1090  MHz Vcc = 36 Volts PW = Note 1 DF = Note 1 F = 1030 MHz	170 7	40	34 10:1	Watts Watts dB %

BVebo BVces h <sub>FE</sub> θjc <sup>2</sup>	Emitter to Base Breakdown Collector to Emitter Breakdown DC - Current Gain Thermal Resistance	Ie = 20 mA Ic = 20 mA Ic = 20 mA, Vce = 5 V	20		0.5	Volts Volts °C/W
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Note 1: MODE- S Pulse Burst, 120  $\mu$ s at 50% Duty, Long term duty = 5%.

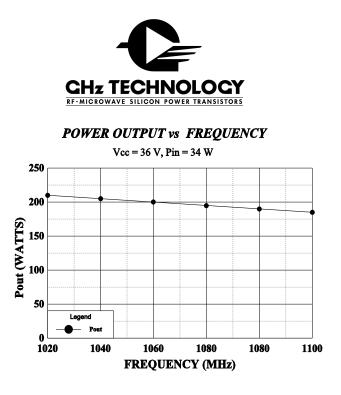
2: At rated pulse conditions

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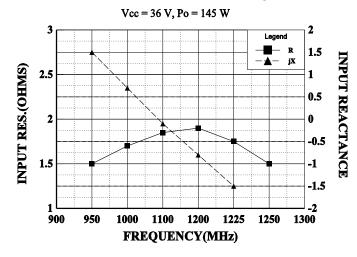
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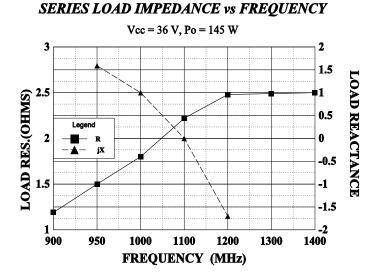
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## SERIES INPUT IMPEDANCE vs FREQUENCY



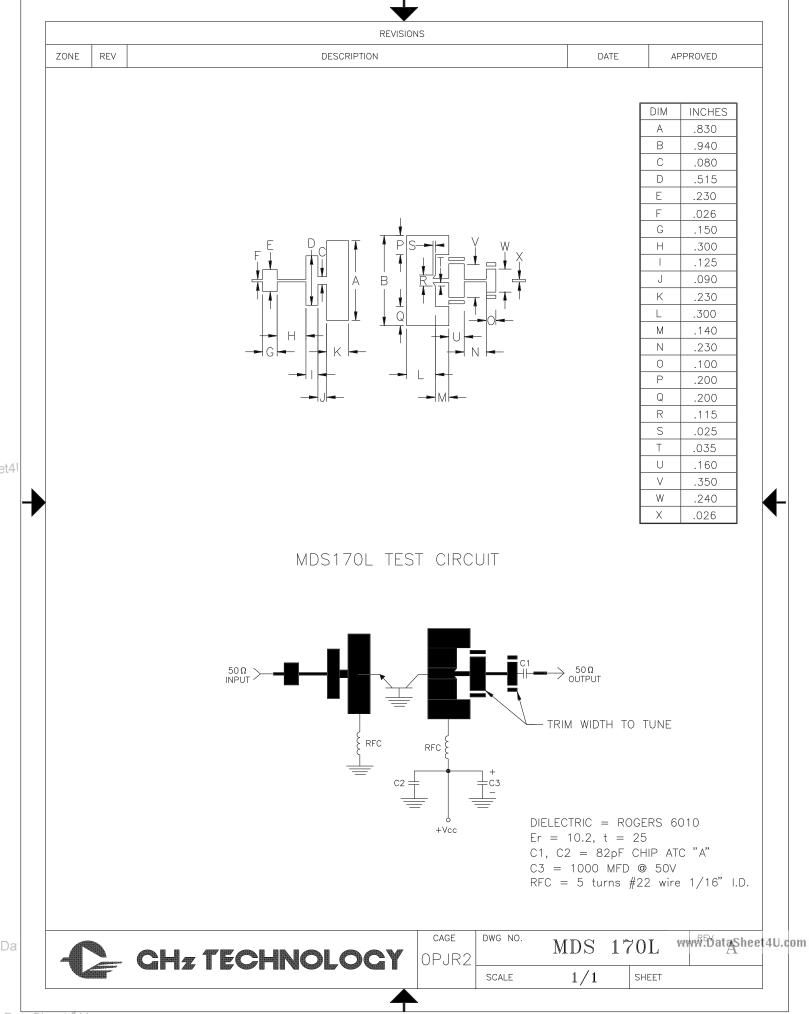
MDS170L



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